

AMENDMENTS TO THE SPECIFICATION

Replacing paragraph [0018] with the following paragraph:

- 5 [0018] The first substrate 18 comprises at least one material selected from a group consisting of GaP, GaAs, Ge, and the like materials. The second substrate 10 comprises at least one material selected from a group consisting of SiC, Al₂O₃, glass materials, quartz, GaP, GaAsP, AlGaAs, and the like materials. The transparent adhesive layer 12 comprises at least one material selected from a group consisting of
- 10 PI, BCB, PFCB, and the like materials. The first reaction layer 11 and the second reaction layer 22 each comprise at least one material selected from a group consisting of SiN_x, Ti, Cr, and the like other materials which will increase adhesion between the material of the first substrate 18 and the transparent adhesive layer 12 and between the second substrate 10 and the transparent adhesive layer 12 through either hydrogen
- 15 bonding or ionic bonding. The first contact layer 13 and the second contact layer 17 each comprise at least one material selected from a group consisting of GaP, GaAs, GaAsP, InGaP, AlGaInP, AlGaAs, and the like materials. The first cladding layer 14, the emitting layer 15, and the second cladding layer 16 each comprise AlGaInP or the like materials. The transparent conductive layer 21 comprises at least one material
- 20 selected from a group consisting of indium tin oxide, cadmium tin oxide, antimony tin oxide, zinc oxide, zinc tin oxide, BeAu, GeAu, Ni/Au, and the like materials.